

What is Claimed is:

1. A method for forming a word line of a semiconductor device, comprising the steps of:

5 (a) forming a sacrificial insulation film on a semiconductor substrate including a device isolation film defining an active region;

(b) selectively etching the sacrificial insulation film to form an I-type sacrificial insulation film pattern
10 on a predetermined region of the active region where a channel region is to be formed;

(c) forming a source/drain region on the semiconductor substrate at both sides of the sacrificial insulation film pattern;

15 (d) forming a first interlayer insulation film on the entire surface;

(e) planarizing the first interlayer insulation film to expose a top surface of the sacrificial insulation film pattern;

20 (f) sequentially forming a insulation film and a second interlayer insulation film on the entire surface;

(g) etching the second interlayer insulation film and insulation film using a word line mask;

(h) removing the sacrificial insulation film pattern

to expose the semiconductor substrate;

(i) growing a gate oxide film on the exposed portion of the semiconductor substrate;

(j) forming a conductive layer on the entire surface;

5 and

(k) planarizing the conductive layer to expose the second interlayer insulation film.

2. The method according to claim 1, wherein the
10 step (h) is a dry etch back process, a wet etch back process or a chemical mechanical polishing.

3. The method according to claim 1, wherein the
step (e) is a dry etch back process or a wet etch back
15 process.

4. The method according to claim 1, wherein the
step (e) is a chemical mechanical polishing.

20 5. The method according to claim 1, wherein the
step (k) is a dry etch back process or a wet etch back process.

6. The method according to claim 1, wherein the

step (k) is a chemical mechanical polishing.